Abstract

METHOD AND APPARATUS FOR INDUCING DC VOLTAGE ON WAFER-FACING ELECTRODE

A method for processing a substrate is disclosed. The method includes supporting the substrate in the plasma-processing chamber configured with a first electrode and a second electrode. The method also includes coupling a passive radio frequency (RF) circuit to the second electrode, the passive RF circuit being configured to adjust one or more of an RF impedance, an RF voltage potential, and a DC bias potential on the second electrode.

Figure: 3